N-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

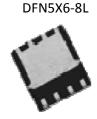
Typical Applications:

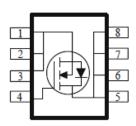
- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
100	15 @ V _{GS} = 10V	15	
	19 @ V _{GS} = 5.5V	14	



FREE





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			100	V			
Gate-Source Voltage	te-Source Voltage						
Continuous Drain Current ^a	T _A =25°C	I _D	15				
Continuous Diain Current	T _A =70°C	טי	13	Α			
Pulsed Drain Current ^b		I _{DM}	50				
Continuous Source Current (Diode Conduction) a		I _S	7.1	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	5	W			
rower dissipation	T _A =70°C	' D	3.2	V V			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	VθJA	65	C/VV			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

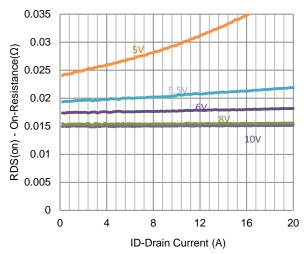
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
Static									
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V			
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA			
Zero Gate Voltage Drain Current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	V _{GS} = 0 V		1	uA			
Zero Gate Voltage Brain Gunerit	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA			
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	25			Α			
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 12 \text{ A}$			15	mΩ			
Dialii-Source Ori-Nesistance	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 10.7 \text{ A}$			19	11122			
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 12 \text{ A}$		20		S			
Diode Forward Voltage	V_{SD}	$I_S = 3.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.73		V			
	Dynamic								
Total Gate Charge	Q_g			56					
Gate-Source Charge	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V}, I_{D} = 12 \text{ A}$		15		nC			
Gate-Drain Charge	Q_gd			36					
Turn-On Delay Time	t _{d(on)}			26					
Rise Time	t _r	$V_{DS} = 50 \text{ V}, R_L = 4.2 \Omega, I_D = 12 \text{ A},$		56		no			
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = 10 V, R_{GEN} = 6 Ω		126		ns			
Fall Time	t _f			61					
Input Capacitance	C _{iss}			4221					
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		392		pF			
Reverse Transfer Capacitance	C_{rss}		·	364					

Notes

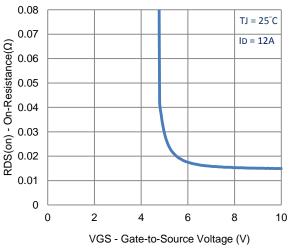
- Pulse test: PW <= 300us duty cycle <= 2%. a.
- Guaranteed by design, not subject to production testing. b.

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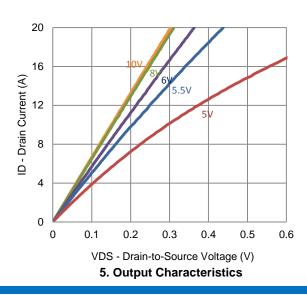
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



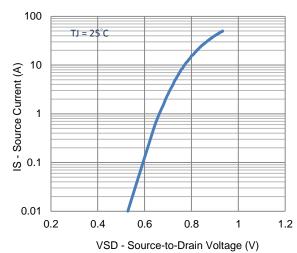
20
TJ = 25°C

16
(4)
Tuesun 12

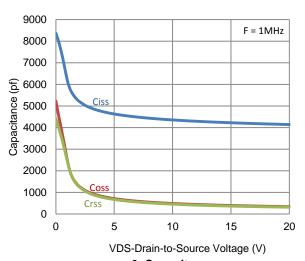
4
0
0
1 2 3 4 5 6 7

VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

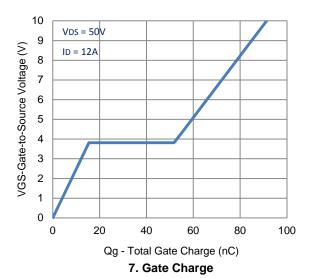


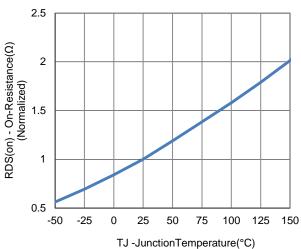
4. Drain-to-Source Forward Voltage



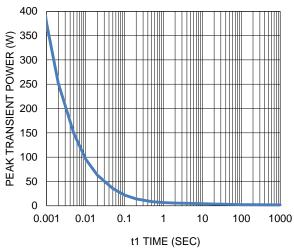
6. Capacitance

Typical Electrical Characteristics





8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

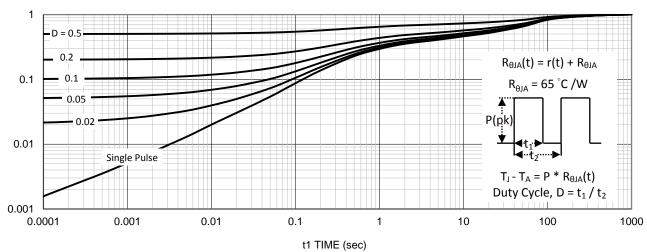
9. Safe Operating Area

100

1000

10

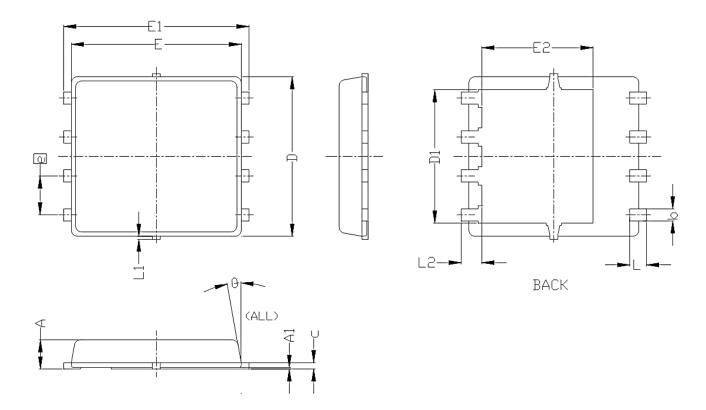
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

0.1

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES			
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.85	0.95	1.00	0.033	0.037	0.039
Al	0.00		0.05	0.000		0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
С	0. 15	0.20	0. 25	0.006	0.008	0.010
D	5. 20 BSC			0. 205 BSC		
D1	4. 35 BSC			0. 171 BSC		
E	5, 55 BSC			0, 219 BSC		
E1	6. 05 BSC			0. 238 BSC		
E2	3. 62 BSC			0. 143 BSC		
e	1. 27 BSC			0. 050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0		0.15	0		0.006
L2	0.68 REF			0. 027 REF		
θ	0°		10°	0°		10°